

# SLA50000/50000H Series

## High Density Gate Array

- Ultra-high-speed, high density and low power consumption
- Low voltage operation: 3.3V and 2.0V
- Number of raw gates: 28,710 to 815,468 gates

### DESCRIPTION

These SLA50000 and SLA50000H Series are high-speed, high-density and powerful drive gate arrays using SOG type CMOS 0.35 $\mu$ m processes. For this Series, we have prepared a product line up of gate arrays ranging from 28,710 through 815,468 of raw gates for immediate applications to large-scale and high-speed systems.

To conform to many application fields with low voltage operation, these gate arrays are compatibly usable for 3V systems and 2V systems. Furthermore, we have prepared low noise output cells of “ $\mu$ A” orders for wide range of applications including miniature portable equipment.

### FEATURES

- Super-high density (adopting 0.35 $\mu$ m silicon gate CMOS with 2-, 3- and 4-metal layers)
- High-speed operation (operation delay of internal gate = 0.140ns at 3.3V, 2-input power NAND standard)
- Internal gate = 3.3 and 2.0V, I/O buffer = 5.0\*\*, 3.3 and 2.0V (built-in level shifter)
- Low power consumption (0.70 $\mu$ W/MHz/BC when internal cell = 3.3V)
- Output drivability (IOL = 100 $\mu$ , 1, 3, 6, 12, 24mA when PCI = 5.0V\*\*, IOL = 100 $\mu$ , 1, 2, 6, 12mA when PCI = 3.3V, IOL = 50 $\mu$ , 300 $\mu$ , 600 $\mu$ , 2, 4, 8mA when 2.0V)
- RAM, PLL\*, IrDA\* and various function cells available
- Low noise output cell, PCI I/F, PECL I/F\*, USB I/F\*, Fail-Safe output\*, JTAG

### PRODUCT LINEUP

Master Features	2-layer Metal	SLA5028	SLA5075	SLA5099	SLA5125	SLA5177	SLA5250	SLA5335	SLA5442	SLA5506	SLA5668	SLA5815
	3-layer Metal	SLA502T	SLA507T	SLA509T	SLA512T	SLA517T	SLA525T	SLA533T	SLA544T	SLA550T	SLA566T	SLA581T
	4-layer Metal	SLA502Q	SLA507Q	SLA509Q	SLA512Q	SLA517Q	SLA525Q	SLA533Q	SLA544Q	SLA550Q	SLA566Q	SLA581Q
Total BCs (Raw Gates)		28,710	75,774	99,198	125,772	177,062	250,160	335,858	442,112	506,688	668,552	815,468
Usable BCs	2-layer Metal	14,355	35,613	46,623	56,597	79,677	112,572	144,418	176,844	202,675	267,420	326,187
	3-layer Metal	25,264	64,407	84,318	100,617	132,796	187,620	251,893	309,478	354,681	467,986	570,827
	4-layer Metal	27,274	71,985	94,238	119,483	168,208	237,652	319,065	397,900	456,019	601,696	733,921
Number of PADs (In Case of Micro Pitch)*		88 (104)	144 (168)	168 (192)	188 (216)	224 (256)	264 (304)	308 (352)	352 (404)	376 (432)	432 (496)	480 (548)
Propagation Delay	Internal Gates	t <sub>pd</sub> = 0.140ns (standard at 3.3V)										
	Input Buffers	TBD										
	Output Buffers	TBD										
I/O Level	CMOS, LVTTTL, PCI, PECL*, USB*											
Input Mode	LVTTTL, CMOS, Pull-up/Pull-down, Schmitt, 2.0/3.3V Level interface (Level shifter)											
Output Mode	Normal, Open drain, 3-state, Bi-directional, 2.0/3.3V Level interface (Level shifter)											

\*Under development \*\*Only SLA50000H Series

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Electric Device Information of EPSON WWW server

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